

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	12	(dislocation with shape\$2 with leakage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/10 08:20
L2	1059	(dislocation with leakage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/10 08:24
L3	517535	(MISFET "field effect transistor" FET MOSFET NMOS PMOS CMOS)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/10 08:25
L4	499	2 and 3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/10 08:26
L5	7429369	(@ad> "20040108" @prad> "20040108" @rlad> "20040108")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/10 08:26
L6	292	4 not 5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/10 08:26
L7	206	4 and concentration not 5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/10 08:28
S1	2	(MISFET "MIS field effect transistor") with (base "substrate") with strained with impurity	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/27 13:19

S2	2	uejima-kazuya\$.in.	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/27 13:20
S3	843	impurity with concentration with depth with transistor	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/27 13:21
S4	7487	MISFET	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/27 13:21
S5	269	MISFET same impurity same depth	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/27 13:22
S6	4	S5 same S4 same S3	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/27 13:22
S7	13	("4007478" "4232439" "4969020" "5254866" "5382536" "5386136" "5441906").PN. OR ("5905284").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/27 13:24
S8	4357	(MISFET "Metal-Insulator Semiconductor Field Effect Transistors")	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/27 13:28
S9	88	(MISFET "Metal-Insulator Semiconductor Field Effect Transistors") with impurity with depth	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/27 13:28
S10	88	(MISFET "Metal-Insulator Semiconductor Field Effect Transistors") with impurity with (depth "Tp")	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/27 13:29
S11	42	(MISFET "Metal-Insulator Semiconductor Field Effect Transistors") with impurity with (depth "Tp") with concentrat\$3	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/27 13:29
S12	3	("6927414" "7141477" "7172935").PN. OR ("7436046").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/27 13:30
S13	10	("20010041432" "20020058385" "5171703" "6184112" "6190179" "6333217" "6368928" "6432802" "6696341").PN. OR ("7141477").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/27 13:42

S14	6	(MISFET "Metal-Insulator Semiconductor Field Effect Transistors") with strained with impurity	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/27 13:48
S15	126	(MISFET "Metal-Insulator Semiconductor Field Effect Transistors") same SiGe	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/27 13:49
S16	126	(MISFET "Metal-Insulator Semiconductor Field Effect Transistors") same SiGe	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/27 13:49
S17	28	(MISFET "Metal-Insulator Semiconductor Field Effect Transistors") same SiGe with concentration	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/27 13:52
S18	10	("20020006058" "20040041217" "20040141367" "20050117617" "20060043443" "5457335" "5659499" "5874760" "6069820" "6753562").PN. OR ("7397071").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/27 13:53
S19	1051	(base "substrate") with (SiGeC)	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/27 14:03
S20	1	(base "substrate") with (SiGeC) with MISFET	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/27 14:04
S21	36	(base "substrate") with (SiGeC) with strained	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/27 14:05
S22	50	(base "substrate") with (SiGeC) with strained	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/27 14:09
S23	252	("5798293" "5461250" "4829346" "5777364" "5821577" "6004137" "6583015" "6690043" "6774390" "6846715" "7033913" "7166867" "7217668" "7417257" "7436046" "20020068393" "20020104993" "20030207571" "20030227036" "20040126958" "20040227186" "20050139891" "20050173738" "20050202640" "20060073664" "20070082470" "20070090373" "20070108514" "20070235802" "20080179752" "5491348" "5497024" "5780328" "5973364" "6174773" "6650565" "6720596" "6847071" "6859381"	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/27 15:16

"6949780" "20020043676"
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"5705835" "5723374"
"5731219" "5767554"
"5828079" "5834851").pn.

S24	549	S3 not (@ad>"20040108" @pd>"20040108")	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/27 15:17
S25	549	S3 not (@ad>"20040108" @pd>"20040108") and impurity	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/27 15:18
S26	549	S3 not (@ad>"20040108" @pd>"20040108") and impurity and depth	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/27 15:18
S27	544	S24 and @py<"2004"	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/27 15:19
S28	195	S23 and MI SFET	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/27 15:20
S29	152	S23 and MI SFET and @py<"2004"	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/27 15:21
S30	88	S23 and MI SFET and @py<"2004" and impurity	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/27 15:21
S31	27	S23 and MI SFET and @py<"2004" and (impurity same depth)	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/27 15:21
S32	30	("5107315" "5173761" "5254862" "5298765").PN. OR ("5382809").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/27 15:23
S33	743295	(base "substrate" same strained same active same concentration).clm.	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/27 15:35
S34	270	(base same gate same impurity same concentration). clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/27 15:36

S35	263	(base same gate same impurity with concentration).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/27 15:37
S36	134	(base with gate with impurity with concentration).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/27 15:37
S37	402	(base with gate with impurity with concentration with source with strained).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/27 15:37
S38	32	(base with gate with impurity with concentration with (strained "channel")).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/27 15:37
S39	3	MISFET with strain\$2 with channel with impurity	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/27 16:58
S40	49	MISFET with strain\$2 with channel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/27 16:59
S41	10	MISFET with strain\$2 with channel and @py< "2004"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/27 16:59
S42	173	("4597160" "4697197" "4841481" "4918510" "4921813" "4992386" "5019882" "5140391" "5272365").PN. OR ("5461250").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/27 16:59
S43	11	TP with impurity with concentration	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 08:32

S44	5751	impurity with concentration with depth	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 08:33
S45	48	impurity with concentration with depth with MIS	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 08:33
S46	26	impurity with concentration with depth with MIS and @py<"2004"	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 08:33
S47	836	impurity with concentration with depth with (source or drain) and @py<"2004"	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 08:36
S48	14	MIS same impurity with concentration with depth with (source or drain) and @py<"2004"	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 08:36
S49	13	("4908327" "4924277" "4956311" "5036019" "5216272" "5334870" "5413945" "5492847" "5532176").PN. OR ("5877531").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/28 08:42
S50	8	("4247861" "4484388" "5005066").PN. OR ("5838048").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/28 08:42
S51	0	MIS same amorphous with layer with depth	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 11:20
S52	0	MIS same amorphous with depth	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 11:21
S53	0	amorphous with channel with depth	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 11:21
S54	80	amorphous with channel with depth	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 11:21

S55	21	impurity with amorphous with channel with depth	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 11:21
S56	2	amorphous near1 layer with channel with depth	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 11:24
S57	1	amorphous adj1 layer with channel with depth	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 12:51
S58	1474	amorphous adj1 layer with (depth "thickness")	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 12:51
S59	55	amorphous adj1 layer with (depth "thickness") with impurity	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 12:51
S60	31	amorphous adj1 layer with (depth "thickness") with impurity and @py<"2004"	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 12:52
S61	0	amorphous adj1 layer with (depth "thickness") with channel with impurity and @py<"2004"	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 12:52
S62	9	amorphous adj1 layer with (depth "thickness") with channel and @py<"2004"	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 12:55
S63	34	amorphous adj1 layer with (depth "thickness") with (source or drain) and @py<"2004"	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 12:56
S64	4	amorphous adj1 layer with (depth "thickness") with (source or drain) with ion and @py<"2004"	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 12:56
S65	34	amorphous adj1 layer with (depth "thickness") with (source or drain) and @py<"2004"	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 12:58

S66	0	amorphous adj1 layer with (depth "thickness") with (source or drain) with maximum and @py<"2004"	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 12:59
S67	6	amorphous with (depth "thickness") with (source or drain) with maximum and @py<"2004"	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 12:59
S68	2	uejima-kazuya	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 13:08
S69	2	uejima-kazuya.in.	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 13:08
S70	2790	(source "drain") with impurity with depth	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 13:59
S71	282	(source "drain") with impurity with depth and MIS	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 13:59
S72	149	(source "drain") with impurity with depth and MIS and @py<"2004"	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 13:59
S73	81	(source "drain") with impurity with depth with concentration and MIS and @py<"2004"	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 14:00
S74	28	(source "drain") with impurity with depth with concentration with channel and MIS and @py<"2004"	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 14:00
S75	6	(source "drain") with impurity with depth with concentration with channel same MIS and @py<"2004"	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 14:00
S76	14	(source "drain") with impurity with depth with channel same MIS and @py<"2004"	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 14:01

S77	24	(source "drain") with impurity with (depth "thickness") with channel same MIS and @py<"2004"	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 14:02
S78	21685	impurity with implant\$3 with region	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 15:47
S79	850	impurity with implant\$3 with region with gate with wall	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 15:48
S80	7	impurity with implant\$3 with region with gate with wall with MIS	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/28 15:48
S81	36	("4442589" "4455738" "4478679").PN. OR ("4597827").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/28 15:50
S82	24	("4312680" "4419809" "4559693" "4597827" "4729966" "4769339" "5001077").PN. OR ("5112766").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/28 15:54
S83	18	("4312680" "4419809" "4597827" "4994904" "5091763" "5108939" "5256586" "5286664" "5541132" "5661048").PN. OR ("5879999").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/28 15:55
S84	841	impurity with implant\$3 with region with thickness	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/28 16:03
S85	389	impurity with implant\$3 with region with thickness with gate	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/28 16:03
S86	1	impurity with implant\$3 with region with thickness with gate with MIS	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/28 16:03
S87	212	impurity with implant\$3 with region with thickness with gate and @py<"2004"	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/28 16:03
S88	1488	impurity with implant\$3 with region with thickness (depth) with (greater) with gate and @py<"2004"	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/28 16:04
S89	1709	impurity with implant\$3 with region with thickness (depth) with (greater "larger") with gate and @py<"2004"	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/28 16:04

S90	883	MIS same impurity with implant\$3 with region with thickness (depth) with (greater "larger") with gate and @py<"2004"	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/28 16:05
S91	881	MIS same wall with impurity with implant\$3 with region with thickness (depth) with (greater "larger") with gate and @py<"2004"	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/28 16:06
S92	881	MIS same strained with impurity with implant\$3 with region with thickness (depth) with (greater "larger") with gate and @py<"2004"	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/28 16:07
S93	7	MIS same (strained with impurity with implant\$3 with region with thickness (depth) with (greater "larger") with gate) and @py<"2004"	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/28 16:07
S94	1	MISFET with abnormal with leakage with current	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/28 16:29
S95	2475535	MISFET with abnormal with I current	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/28 16:29
S96	6	MISFET with abnormal with current	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/28 16:30
S97	2	uejima-kazuya.in.	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/29 09:45
S98	89	kubo-minoru.in.	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/29 09:57
S99	62	kubo-minoru.in. and @py<"2004"	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/29 09:57
S100	6198	(source "drain") with (plasma "gas") with dop\$3	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/29 10:29
S101	979	(source "drain") with (plasma "gas") with impurity with dop \$3	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/29 10:30

S102	532	(source "drain") with (plasma "gas") with impurity with dop \$3 and @py<"2004"	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/29 10:30
S103	79	(source "drain") with (plasma "gas") with impurity with dop \$3 same transistor and @py<"2004"	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/29 10:30
S104	6	("4733284" "4864376").PN. OR ("5864149").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/29 10:31
S105	1580	(source "drain") with low with impurity with gate and @py<"2004"	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/29 13:15
S106	57	(source "drain") with low with impurity with gate with "near" and @py<"2004"	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/29 13:16
S107	31	(source with drain) with low with impurity with gate with "near" and @py<"2004"	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/29 13:25
S108	37	(source with drain) with low with impurity with concentration with "near" and @py<"2004"	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/29 13:25
S109	36	MISFET with strained with channel	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/29 15:08
S110	49	("4442449" "4975387" "5218213" "5521108" "5759898" "6059895" "6228692").PN. OR ("6607948").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/29 15:12
S111	115	257/288.ccls. and MISFET	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/29 15:14
S112	618047	257/288, "190", "616".ccls. and (MISFET with strained with channel)	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/29 15:15
S113	618047	257/288, "190", "616".ccls. and (MISFET with strained with channel with impurity)	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/29 15:15
S114	618047	257/288, "190", "616".ccls. and (MISFET with strained near1 channel with impurity)	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/29 15:15
S115	618047	257/288, "190", "616".ccls. and (MISFET)	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/29 15:16
S116	2866	257/288, "616".ccls. and (MISFET)	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/29 15:16
S117	2866	257/288, "616".ccls. and (MISFET) and @py<"2004"	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/29 15:16

S118	29	257/616.ccls. and (MISFET)	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/29 15:16
S119	107	257/192.ccls. and (MISFET)	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/29 15:19
S120	81	257/192.ccls. and (MISFET)	USPAT	OR	ON	2008/10/29 15:20
S121	58	257/288.ccls. and (MISFET)	USPAT	OR	ON	2008/10/29 15:21
S122	1	257/288.ccls. and (MISFET with strained)	USPAT	OR	ON	2008/10/29 15:21
S123	289814	257/288, "192", "616".ccls. and (MISFET with strained)	USPAT	OR	ON	2008/10/29 15:21
S124	1964	257/288, "616".ccls. and (MISFET with strained)	USPAT	OR	ON	2008/10/29 15:21
S125	4	"257"/"616".ccls. and (MISFET with strained)	USPAT	OR	ON	2008/10/29 15:21
S126	7	"257"/"192".ccls. and (MISFET with strained)	USPAT	OR	ON	2008/10/29 15:22
S127	74	"20040135210" 20030227029* "6633066" "6190975"	USPAT	OR	ON	2008/10/29 15:42
S128	3	("20040135210" 20030227029* "6633066" "6190975").pn.	US-PGPUB; USPAT	OR	ON	2008/10/29 15:42
S129	4	("20040135210" "20030227029" "6633066" "6190975").pn.	US-PGPUB; USPAT	OR	ON	2008/10/29 15:44
S130	4	"7141477"	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/31 13:26
S131	0	"2020058385"	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/31 13:27
S132	2	"20020058385"	US-PGPUB; USPAT; USOCR; EPO; DERWENT; IBM_TDB	OR	ON	2008/10/31 13:27
S133	1640	maximum with concentration with depth	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/08 13:40

S134	1104	gate with (source drain) with strain\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/08 13:40
S135	1	S133 same S134	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/08 13:41
S136	5	S133 and S134	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/08 13:41
S137	7424565	(@ad> "20040108" @prad> "20040108" @rlad> "20040108")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/08 13:43
S138	8	("20040135210" "20030227029" "6633066" "6190975").pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/08 13:49
S139	5	(kazuya with uejima).in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/09 14:59
S140	8	("20030227029" "20040075143" "20020011617" "20020105015" "6190975"). pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/09 15:05
S141	9851	MISFET	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/09 16:29
S142	28662	concentration with depth	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/09 16:29

S143	76	S141 with S142	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/09 16:30
S144	171	(strain\$2 and gate and electrode and concentration). clm.	US-PGPUB; USPAT	OR	ON	2009/04/09 16:57
S145	26	(strain\$2 and gate and electrode and concentration and depth).clm.	US-PGPUB; USPAT	OR	ON	2009/04/09 16:57
S146	135	(strain\$2 and (source drain) and (dielectric insulat\$3) and depth).clm.	US-PGPUB; USPAT	OR	ON	2009/04/09 16:59
S147	31	(strain\$2 and (source drain) and (dielectric insulat\$3) and depth and concentration).clm.	US-PGPUB; USPAT	OR	ON	2009/04/09 17:00

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